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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/058,578	01/28/2002	Eiji Yamada	245402004200	4309

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755 PAGE MILL RD  
PALO ALTO, CA 94304-1018

EXAMINER
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LOUIE, WAI SING

ART UNIT	PAPER NUMBER
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2814

DATE MAILED: 04/01/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

**Office Action Summary**

Application No.

10/058,578

Applicant(s)

YAMADA, EIJI

Examiner

Wai-Sing Louie

Art Unit

2814

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 30 January 2003.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 1-9 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-9 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

**Priority under 35 U.S.C. §§ 119 and 120**

- 13) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some \* c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

**Attachment(s)**

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) \_\_\_\_\_
- 4) ☐ Interview Summary (PTO-413) Paper No(s). \_\_\_\_\_
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: \_\_\_\_\_

## DETAILED ACTION

### *Claim Rejections - 35 USC § 103*

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1-9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ogawa et al. (US 6,455,877) in view of Goetz et al. (US 6,441,393).

With regard to claims 1 and 3, Ogawa et al. disclose a group III-V light-emitting device (col. 6, line 23 to col. 24, line 51 and fig. 1) comprising:

- A silicon doped n-type GaN-based substrate 1002 (col. 12, lines 60-65);
- A semiconductor stacked-layer structure including a plurality of nitride-based semiconductor layers 1003 to 1010 grown on the GaN-based substrate 1002 by MOCVD (col. 13, lines 30-47);
- Ogawa et al. do not disclose the GaN-based substrate having an interface region contacting the semiconductor stacked-layer structure, where the interface region containing oxygen atoms. However, Goetz et al. disclose the GaN layer is doped with silicon and co-doped with oxygen (Goetz col. 3, lines 36-48). Goetz et al. teach the Si doping causes the formation of cracks (Goetz col. 1, lines 20-24) and the co-doping with oxygen stabilizes the structure and improve conductivity of the Group III-V nitride materials (Goetz col. 2, lines 47-53). Therefore, it would

have been obvious at the time the invention was made to modify Ogawa's device with the teaching of Goetz et al. to provide oxygen dopant at the interface region contacting the semiconductor stacked-layer structure. Doing so would alleviate cracking and improve conductivity of the structure. Ogawa et al. disclose the concentration at least  $3 \times 10^{18} \text{ cm}^{-3}$  (col. 4, line 46).

With regard to claims 2 and 7, Ogawa et al. disclose when the GaN-based substrate was made, GaCl was generated and would mixed by the impurity doping gas. Therefore, the GaN-based substrate inherently contains chlorine (col. 9, lines 5-15).

With regard to claim 4, Ogawa et al. disclose the plurality of nitride-based semiconductor layers included in the semiconductor stacked-layer structure include a layer 1003 contacting the GaN-based substrate 1002 (fig. 11), and the layer contacting the GaN-based substrate contains oxygen (oxygen doped col. 8, line 3).

With regard to claims 5 and 8-9, Ogawa et al. disclose a group III-V light-emitting device (col. 6, line 23 to col. 24, line 51 and fig. 1) comprising:

- A GaN-based substrate 2402 including a p-type impurity (col. 18, line 61 to col. 19, line 2);
- A semiconductor stacked-layer structure including a plurality of nitride-based semiconductor layers 2403 to 2410 grown on the GaN-based substrate 2402 by MOCVD (col. 19, lines 2-14);
- Ogawa et al. do not disclose the GaN-based substrate having an interface region contacting the semiconductor stacked-layer structure, where the interface region containing oxygen atoms. However, Goetz et al. disclose the GaN layer is doped

with silicon and co-doped with oxygen (Goetz col. 3, lines 36-48). Goetz et al. teach the Si doping causes the formation of cracks (Goetz col. 1, lines 20-24) and the co-doping with oxygen stabilizes the structure and improve conductivity of the Group III-V nitride materials (Goetz col. 2, lines 47-53). Therefore, it would have been obvious at the time the invention was made to modify Ogawa's device with the teaching of Goetz et al. to provide oxygen dopant at the interface region contacting the semiconductor stacked-layer structure. Doing so would alleviate cracking and improve conductivity of the structure. Ogawa et al. disclose the concentration at least  $3 \times 10^{18} \text{ cm}^{-3}$  (col. 4, line 46).

With regard to claim 6 and in according to claim 5 above, Ogawa et al. disclose the p-type impurity includes magnesium (col. 9, line 63).

### ***Response to Arguments***

Applicant's arguments filed 10/9/02 have been fully considered but they are not persuasive.

- Applicant argues that Ogawa et al. do not disclose "a silicon doped n-type GaN-based substrate". However, Ogawa et al. disclose "a silicon doped n-type GaN-based substrate" (col. 12, lines 60-65).
- Applicant argues that Ogawa et al. do not disclose "the GaN-based substrate having an interface region contacting the semiconductor stacked structure containing oxygen atoms". However, Ogawa et al. modified by Goetz et al. in

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claims 1 and 5, would disclose the oxygen atoms at the interface region. Please see above rejection.

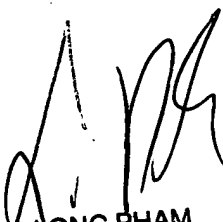
Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wai-Sing Louie whose telephone number is (703) 305-0474. The examiner can normally be reached on 7:30 AM to 4:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

wsl

March 24, 2003

  
LONG PHAM  
PRIMARY EXAMINER